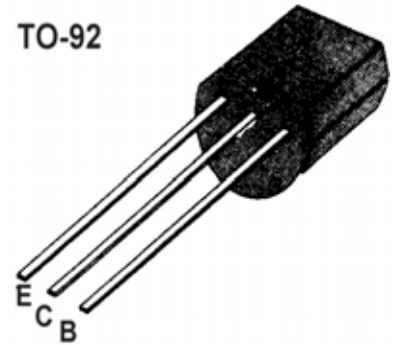


■■ APPLICATION: General Purpose Amplifier Application.

■■ MAXIMUM RATING (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	160	V
Collector-emitter voltage	V _{CEO}	160	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	5~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BV _{CBO}	160			V	I _C = 10uA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	160			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 10uA, I _C =0
Collector Cut-off Current	I _{CBO}			10	μA	V _{CB} = 140V, I _E =0
Emitter Cut-off Current	I _{EBO}			10	μA	V _{EB} = 4V, I _C =0
Common Emitter DC Current Gain	h _{FE}	60		200		V _{CE} = 5V, I _C = 10mA
Common Emitter DC Current Gain	h _{FE1}					V _{CE} = 5V, I _C = 1mA
Base-Emitter Voltage	V _{BE}			1.5	V	I _C = 10mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.5	V	I _C = 30mA, I _B = 3mA
Gain bandwidth product	f _T		140		MHZ	I _C = 10mA, V _{CE} = 5V
Common Base Output Capacitance	C _{ob}		3.8		PF	V _{CB} = 10V, I _E =0, f = 1MHZ

■■ h_{FE} Classification

Classification	B	C
h _{FE}	60~120	100~200